**Vishay Semiconductors** 

## Phase Control Thyristors (Hockey PUK Version), 1473 A



K-PUK (A-24)

PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	1473 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	1200 V, 1400 V, 1600 V, 1800 V, 2000 V, 2200 V, 2400 V				
V <sub>TM</sub>	1.80 V				
I <sub>GT</sub>	100 mA				
TJ	-40 °C to +125 °C				
Package	K-PUK (A-24)				
Circuit configuration	Single SCR				

#### **FEATURES**

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case K-PUK (A-24)
- High profile hockey PUK
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### **TYPICAL APPLICATIONS**

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		1473	A			
I <sub>T(AV)</sub>	T <sub>hs</sub>	55	°C			
<b>I</b>		2913	A			
I <sub>T(RMS)</sub>	T <sub>hs</sub>	25	°C			
I	50 Hz	20.0	- A			
ITSM	60 Hz	21.2				
l <sup>2</sup> t	50 Hz	2000	kA <sup>2</sup> s			
1-1	60 Hz	1865	KAES			
l²√t		20 000	kA²√s			
V <sub>DRM</sub> /V <sub>RRM</sub>	Range	1200 to 2400	V			
t <sub>q</sub>	Typical	300	μs			
TJ	Range	-40 to +125	°C			

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I <sub>RRM</sub> MAXIMUM AT T <sub>J</sub> = 125 °C mA			
	12	1200	1300				
	14	1400	1500				
	16	1600	1700				
VS-ST1000CK	18	1800	1900	100			
	20	2000	2100				
	22	2200	2300				
	24	2400	2500				

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ABSOLUTE MAXIMUM RATINGS	5						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS	
Maximum average on-state current	L	180° condu	ction, half sine v	wave	1473 (630)	A	
at heatsink temperature	I <sub>T(AV)</sub>	Double side	e (single side) co	ooled	55 (85)	°C	
Maximum RMS on-state current	I <sub>T(RMS)</sub>	DC at 25 °C	heatsink temp	erature double side cooled	6540	А	
		t = 10 ms	No voltage		20.0		
Maximum peak, one-cycle,	l	t = 8.3 ms	reapplied		21.2	kA kA kA <sup>2</sup> s	
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		17.0		
		t = 8.3 ms	reapplied	Sinusoidal half wave,	18.1		
	l <sup>2</sup> t	t = 10 ms	No voltage	initial T <sub>J</sub> = T <sub>J</sub> maximum	2000		
Maximum I <sup>2</sup> t for fusing		t = 8.3 ms	reapplied		1865		
Maximum Pt for fusing		t = 10 ms	100 % V <sub>RRM</sub>		1445		
		t = 8.3 ms	reapplied		1360		
Maximum I <sup>2</sup> $\sqrt{t}$ for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied			20 000	kA²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x π	(16.7 % x $\pi$ x I <sub>T(AV)</sub> < I < $\pi$ x I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum			v	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi x I_{T(AV)}), T_J = T_J maximum$			1.024	v	
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x I <sub>T(AV)</sub> < I < $\pi$ x I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum			0.283	mΩ	
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			0.265	11122	
Maximum on-state voltage drop	V <sub>TM</sub>	$I_{pk}$ = 3000 A, $T_J$ = 125 °C, $t_p$ = 10 ms sine pulse			1.80	V	
Maximum holding current	I <sub>H</sub>	$T_{J} = 25 \text{ °C}$ , anode supply 12 V resistive load			600	m 4	
Typical latching current	١L	ij=25 C,	anoue supply 1		1000	- mA	

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,t_r \leq 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\leq 80~\%~V_{DRM}$	1000	A/µs		
Typical delay time	t <sub>d</sub>	Gate current 1 A, dl <sub>g</sub> /dt = 1 A/ $\mu$ s V <sub>d</sub> = 0.67 % V <sub>DRM</sub> , T <sub>J</sub> = 25 °C	1.9			
Typical turn-off time t <sub>q</sub>		$\begin{split} I_{TM} &= 550 \text{ A},  T_J =  T_J \text{ maximum, dI/dt} = 40 \text{ A/} \mu \text{s}, \\ V_R &= 50 \text{ V},  \text{dV/dt} = 20 \text{ V/} \mu \text{s}, \text{ gate } 0 \text{ V} 100 \ \Omega,  t_p = 500 \ \mu \text{s} \end{split}$	300	μs		

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum critical rate of rise of of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated $V_{DRM}$	500	V/µs		
Maximum peak reverse and off-state leakage current	I <sub>RRM</sub> , I <sub>DRM</sub>	$T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied	100	mA		



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TRIGGERING						
DADAMETED		SYMBOL TEST CONDITIONS		VALUES		
PARAMETER	STMBOL			TYP.	MAX.	UNITS
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	16		w
Maximum peak average gate power	P <sub>G(AV)</sub>	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	:	3	vv
Maximum peak positive gate current	I <sub>GM</sub>			3	.0	А
Maximum peak positive gate voltage	+V <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le 5$ ms		20		V
Maximum peak negative gate voltage	-V <sub>GM</sub>			5.0		
	I <sub>GT</sub>	T <sub>J</sub> = -40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units	200	-	
DC gate current required to trigger		T <sub>J</sub> = 25 °C		100	200	mA
		T <sub>J</sub> = 125 °C		50	-	
		T <sub>J</sub> = -40 °C		1.4	-	
DC gate voltage required to trigger	V <sub>GT</sub>	T <sub>J</sub> = 25 °C	12 V anode to cathode applied	1.1	3.0	V
		T <sub>J</sub> = 125 °C		0.9	-	
DC gate current not to trigger	I <sub>GD</sub>	T. T. movimum	Maximum gate current/voltage not to trigger is the maximum	10		mA
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J maximum$	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.	25	v

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		UNITS	
Maximum operating temperature range	TJ		-40 to +125	°C	
Maximum storage temperature range	T <sub>Stg</sub>		-40 to +150	Ĵ	
Maximum thermal resistance,	D	DC operation single side cooled	0.042		
junction to heatsink	R <sub>thJ-hs</sub>	DC operation double side cooled	0.021	K/W	
Maximum thermal resistance,	Б	DC operation single side cooled	0.006	r\/ vv	
case to heatsink	R <sub>thC-hs</sub>	DC operation double side cooled	0.003		
Mounting force, ± 10 %			24 500	Ν	
			(2500)	(kg)	
Approximate weight			425	g	
Case style		See dimensions - link at the end of datasheet	K-PUK (A	-24)	

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEAT CONDITIONS	UNITS
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS
180°	0.003	0.003	0.002	0.002		
120°	0.004	0.004	0.004	0.004	T <sub>J</sub> = T <sub>J</sub> maximum	K/W
90°	0.005	0.005	0.005	0.005		
60°	0.007	0.007	0.007	0.007		
30°	0.012	0.012	0.012	0.012		

#### Note

• The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

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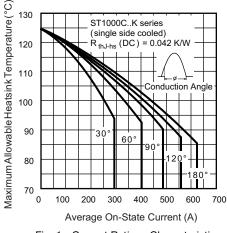


Fig. 1 - Current Ratings Characteristics

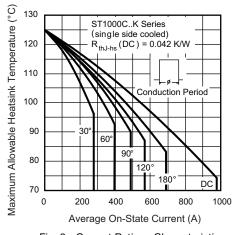


Fig. 2 - Current Ratings Characteristics

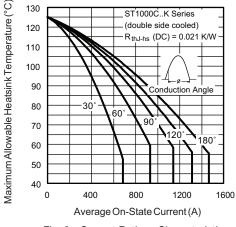
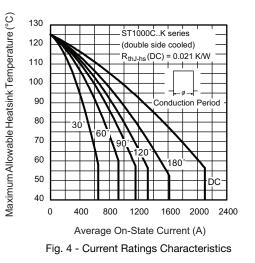


Fig. 3 - Current Ratings Characteristics

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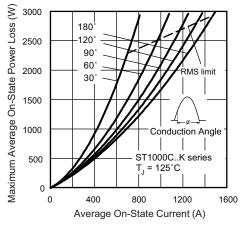


Fig. 5 - On-State Power Loss Characteristics

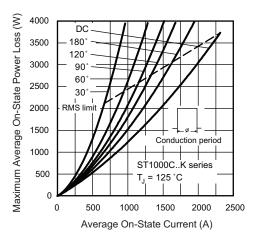


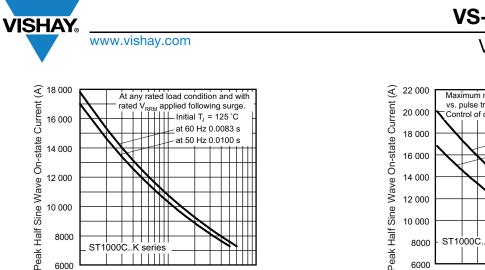
Fig. 6 - On-State Power Loss Characteristics

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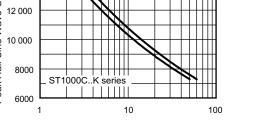
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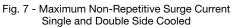
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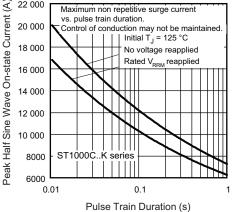


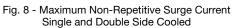
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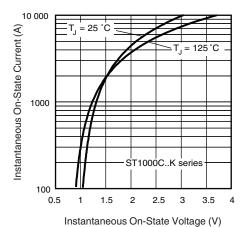


Number Of Equal Amplitude Half Cycle Current Pulses (N)











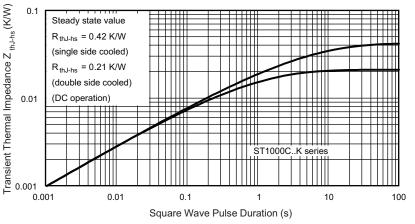
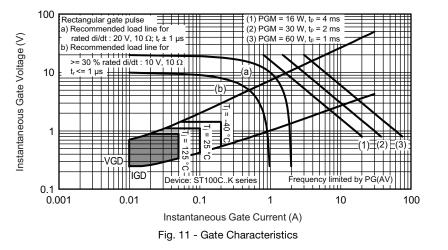


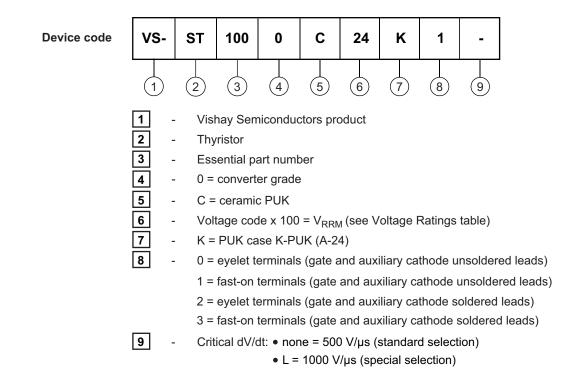
Fig. 10 - Thermal Impedance ZthJ-hs Characteristics

## **Vishay Semiconductors**



#### **ORDERING INFORMATION TABLE**

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LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95081			

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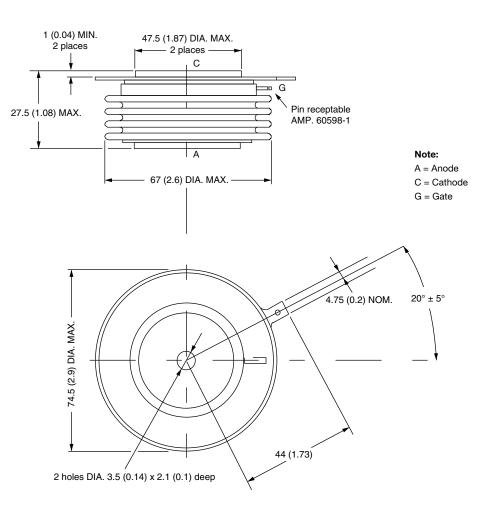


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# K-PUK (A-24)

#### **DIMENSIONS** in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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